

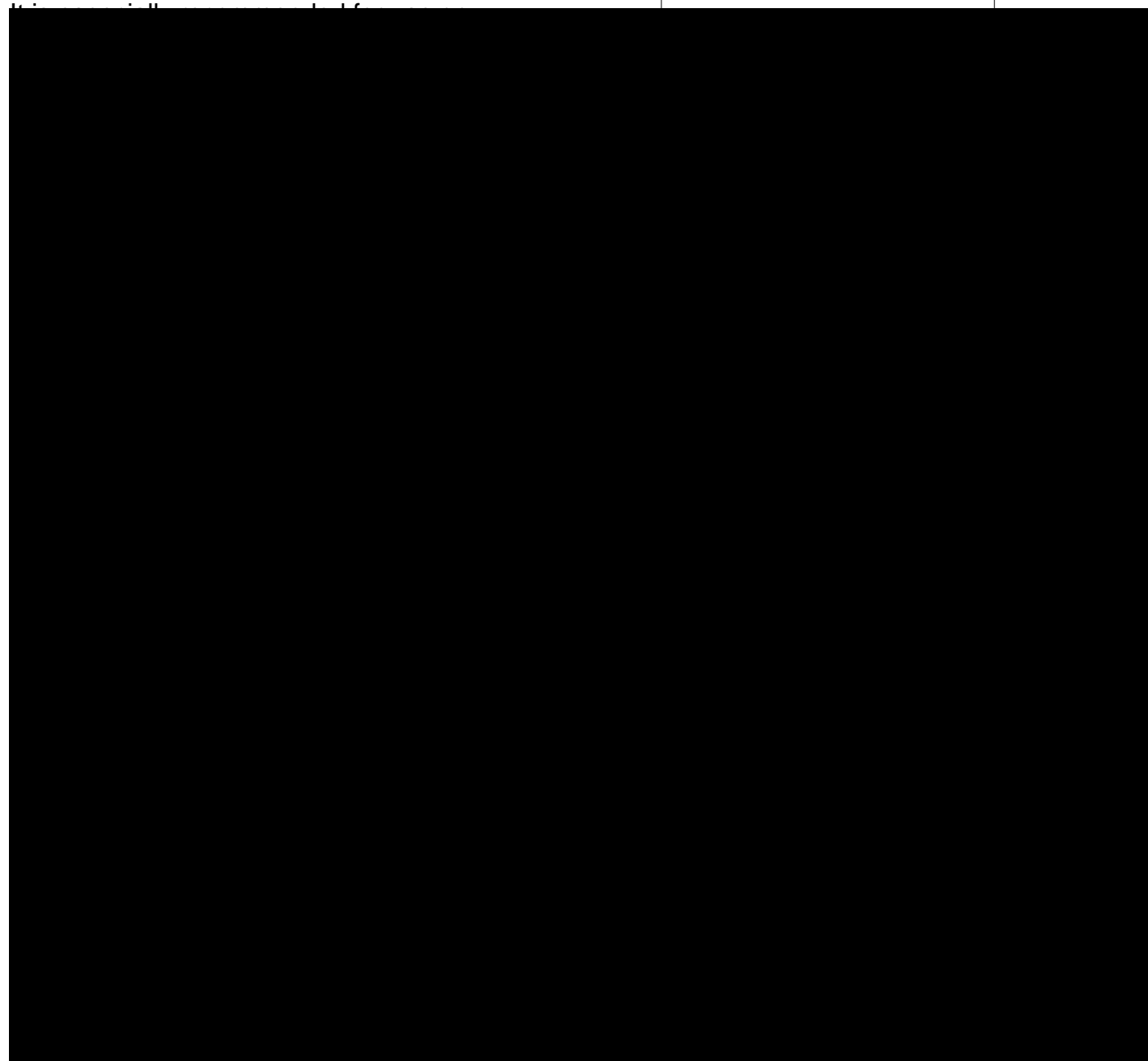
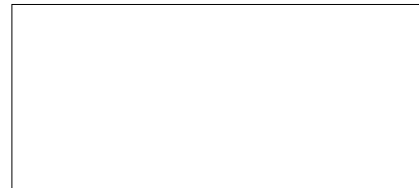


JCT616E 16A SCR

Rev.A.1.1

DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT616E of silicon controlled rectifiers provides high dV/dt rate with strong resistance to electromagnetic interference.



Critical rate of rise of on-state current ( $I_G=2 \times I_{GT}$ , $f=100\text{Hz}$ , $T_j=125$ )	di/dt	150	A s
Peak gate current ( $t_p$ )			

Average gate power dissipation ( $T_j=125$ )	$P_{G(AV)}$	1	W
Peak gate power	$P_{GM}$	20	W
Peak pulse voltage ( $T_j=25$ ; non-repetitive, off-state; FIG.8)	$V_{pp}$	0.5	kV

## ELECTRICAL CHARACTERISTICS (unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
$I_{GT}$	$V_D=12V$ $R_L=33$	-	-	15	mA
$V_{GT}$		-	-	1	V
$V_{GD}$	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k$	0.2	-	-	V
$I_L$	$I_G=1.2I_{GT}$	-	-	60	mA
$I_H$	$I_T=500mA$	-	-	50	mA
dV/dt	$V_D=400V$ Gate Open $T_j=125$	1200	-	-	V/s
$t_{on}$	$I_G=20mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25$	-	4	-	s
$t_{off}$		-	60	-	

## STATIC CHARACTERISTICS

Symbol

JCT616E

J

JCT616E

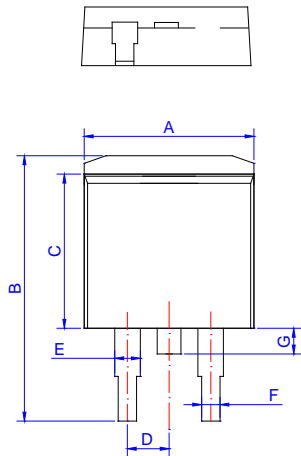
JCT616E

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PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.40		9.60	0.370		0.378
D	2.40			0.094		
E	1.20		1.50	0.047		0.059
F	0.75		0.85	0.029		0.033

DELIVERY MODE

